Product data sheet

1. General description

Planar passivated very sensitive gate four quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in general purpose bidirectional switching and phase control applications, where high sensitivity is required in all four quadrants. This very sensitive gate "series D" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

2. Features and benefits

- · High blocking voltage capability
- · Direct triggering from low power drivers and logic ICs
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants
- · Low holding current for low current loads and lowest EMI at commutation
- · Very sensitive gate

3. Applications

- General purpose motor control
- · General purpose switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	eter Conditions			Values			
Absolute	maximum rating							
V_{DRM}	repetitive peak off-state voltage		600				V	
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 102 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3		8			А	
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5	65 A			А		
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Static ch	aracteristics							
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G+;}$ $T_j = 25 \text{ °C; } Fig. 7$		-	2.5	5	mA	
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$		-	3.5	5	mA	
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 7$		-	3.5	5	mA	
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G+;} $ $T_j = 25 \text{ °C; } Fig. 7$		-	6.5	10	mA	
I _H	holding current	V _D = 12 V; T _j = 25 °C; ; <u>Fig. 9</u>		-	1.5	10	mA	

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	
2	T2	main terminal 2		T2_D_T1
3	G	gate		sym051
mb	T2	mounting base; main terminal 2		Symoor
			1 2 3	

6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
BT137-600D	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78				

7. Marking

Table 4. Marking codes

Type number	Marking codes
BT137-600D	BT137-600D

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{DRM}	repetitive peak off-state voltage		600	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 102 °C; Fig 1; Fig 2; Fig 3	8	Α
I _{TSM}	non-repetitive peak on- state current	full sine wave; T _{j(init)} = 25 °C; t _p = 20 ms; <u>Fig 4</u> ; <u>Fig 5</u>	65	А
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	71	Α
l²t	I ² t for fusing	$t_p = 10 \text{ ms; SIN}$	21	A ² s
dl _⊤ /dt	t rate of rise of on-state	I _G = 10 mA; T2+ G+	50	A/µs
	current	I _G = 10 mA; T2+ G-	50	A/µs
		I _G = 10 mA; T2- G-	50	A/µs
		I _G = 20 mA; T2- G+	10	A/µs
I _{GM}	peak gate current		2	А
P_{GM}	peak gate power		5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.5	W
T _{stg}	storage temperature		-40 to 150	°C
T _j	junction temperature		125	°C

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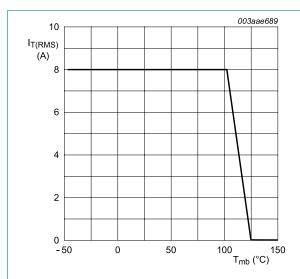
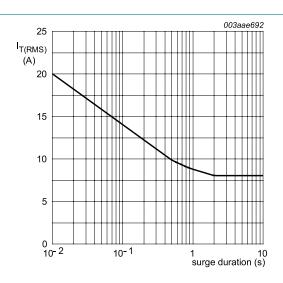
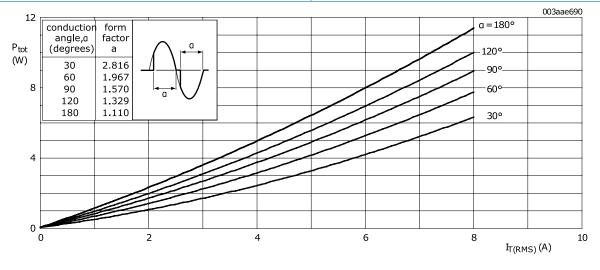


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



f = 50 Hz; $T_{mb} \le 102 \, ^{\circ}\text{C}$

Fig. 2. RMS on-state current as a function of surge duration; maximum values

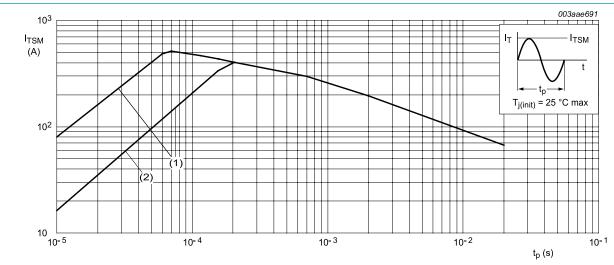


 α = conduction angle

 $a = form factor = I_{T(RMS)} / I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

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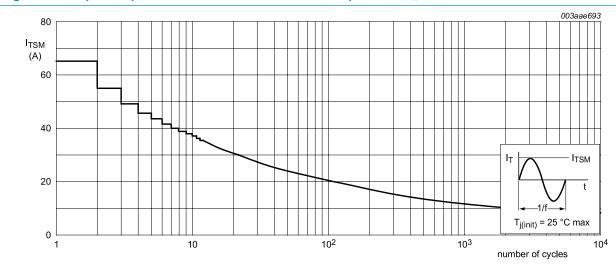


 $t_p \le 20 \text{ ms}$

 $(1) dI_T/dt limit$

(2) T2- G+ quadrant limit

Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values



f = 50 Hz

Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance	full cycle; Fig 6		-	-	2	K/W
	from junction to mounting base	half cycle; <u>Fig 6</u>		-	-	2.4	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air		-	60	-	K/W

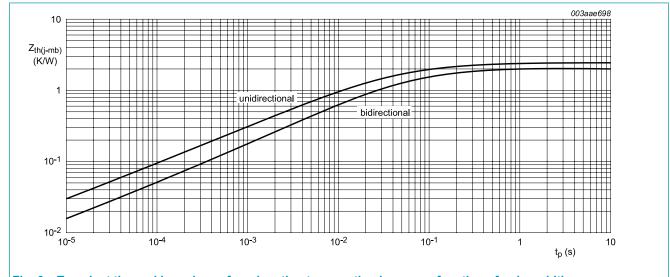


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

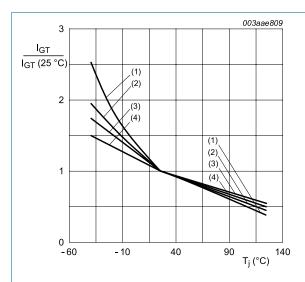
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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
I _{GT} gate trigger current		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	2.5	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$	-	3.5	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 7}}$	-	3.5	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	6.5	10	mA
l _L	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	1.6	15	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	8.5	20	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	1.2	15	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	2.5	20	mA
I _H	holding current	$V_D = 12 \text{ V}; T_j = 25 \text{ °C}; Fig. 9$	-	1.5	10	mA
V _T	on-state voltage	I _T = 10 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.65	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 11	0.25	0.4	-	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics		,	,		
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; R_{GT1} = 1 k Ω ; exponential waveform	-	5	-	V/µs
t _{gt}	gate-controlled turn-on time	$I_{TM} = 12 \text{ A}; V_D = 600 \text{ V}; I_G = 0.1 \text{ A}; dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs

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- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

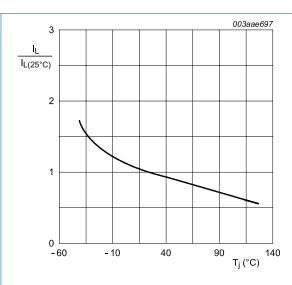


Fig. 8. Normalized latching current as a function of junction temperature

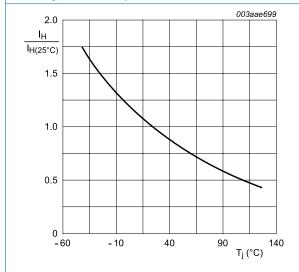
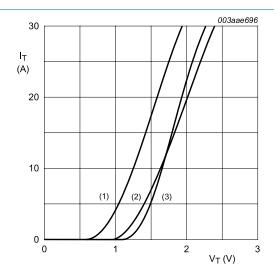


Fig. 9. Normalized holding current as a function of junction temperature



 V_o = 1.264 V; R_s = 0.038 Ω

(1) T_j = 125 °C; typical values

(2) $T_j = 125$ °C; maximum values

(3) T_i = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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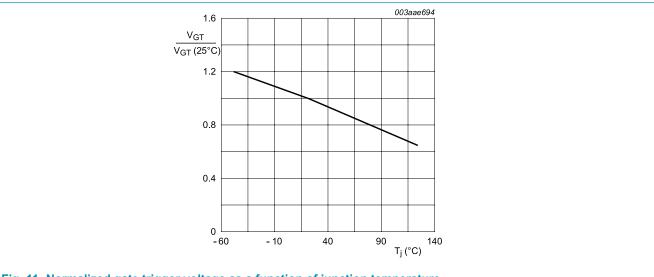
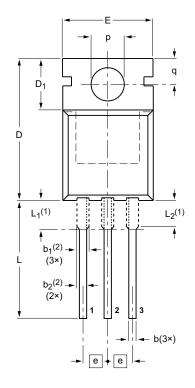


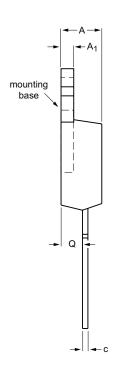
Fig. 11. Normalized gate trigger voltage as a function of junction temperature

11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78





0 5 10 mm

DIMENSIONS (mm are the original dimensions)

UNIT	Α	A ₁	b	b ₁ ⁽²⁾	b ₂ ⁽²⁾	С	D	D ₁	E	е	L	L ₁ ⁽¹⁾	L ₂ ⁽¹⁾ max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

- $1. \ Lead \ shoulder \ designs \ may \ vary.$
- 2. Dimension includes excess dambar.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13	

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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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